

# PS9031

R08DS0131EJ0200

Rev.2.00

2.5 A OUTPUT CURRENT, HIGH CMR, IGBT GATE DRIVE,  
5-PIN SOP (LSO5 WITH 8mm CREEPAGE DISTANCE) PHOTOCOUPLER

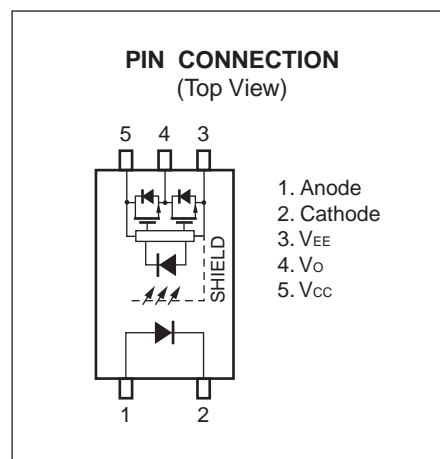
Mar 11, 2016

## DESCRIPTION

The PS9031 is an optically coupled isolator containing a GaAlAs LED on the input side and a photodiode, a signal processing circuit and power MOSFETs on the output side on one chip.

## FEATURES

- Long creepage distance (8 mm MIN.)
- Large peak output current (2.5 A MAX., 2.0 A MIN.)
- High speed switching ( $t_{PLH}$ ,  $t_{PHL}$  = 175 ns MAX.)
- UVLO (Under Voltage Lock Out) protection with hysteresis
- High common mode transient immunity ( $CM_H$ ,  $CM_L$  =  $\pm 50$  kV/ $\mu$ s MIN.)
- Operating Ambient Temperature (125 °C MAX.)
- Embossed tape product : PS9031-F3 : 3000 pcs/reel
- Pb-Free product
- Safety standards
  - UL approved: UL1577, Double protection
  - CSA approved: CA5A, CAN/CSA-C22.2 No.60065, CAN/CSA-C22.2 No.60950-1, Reinforced insulation
  - VDE approved: DIN EN 60747-5-5 (Option)



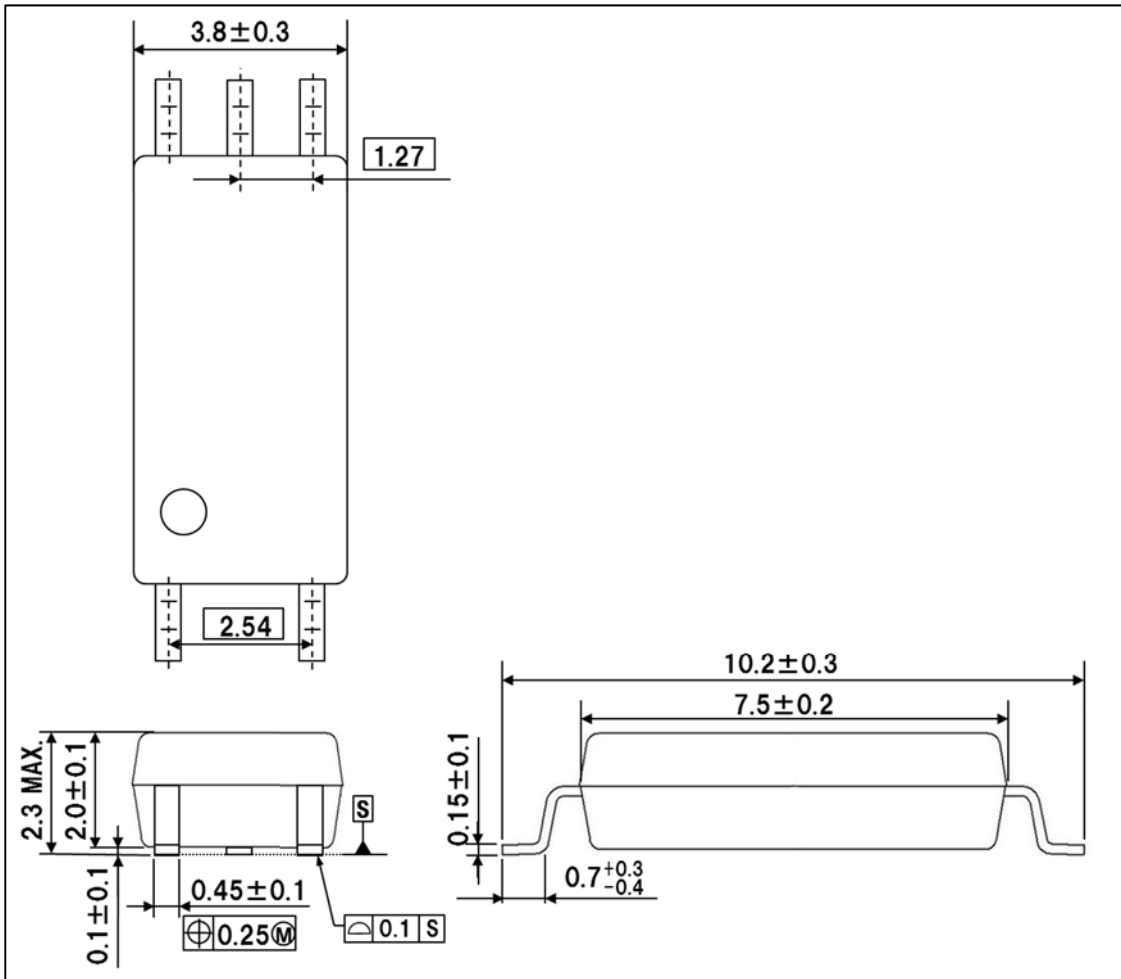
## APPLICATIONS

- IGBT, Power MOS FET Gate Driver
- Industrial inverter
- AC Servo

Start of mass production

Oct.2015

## PACKAGE DIMENSIONS (UNIT: mm)

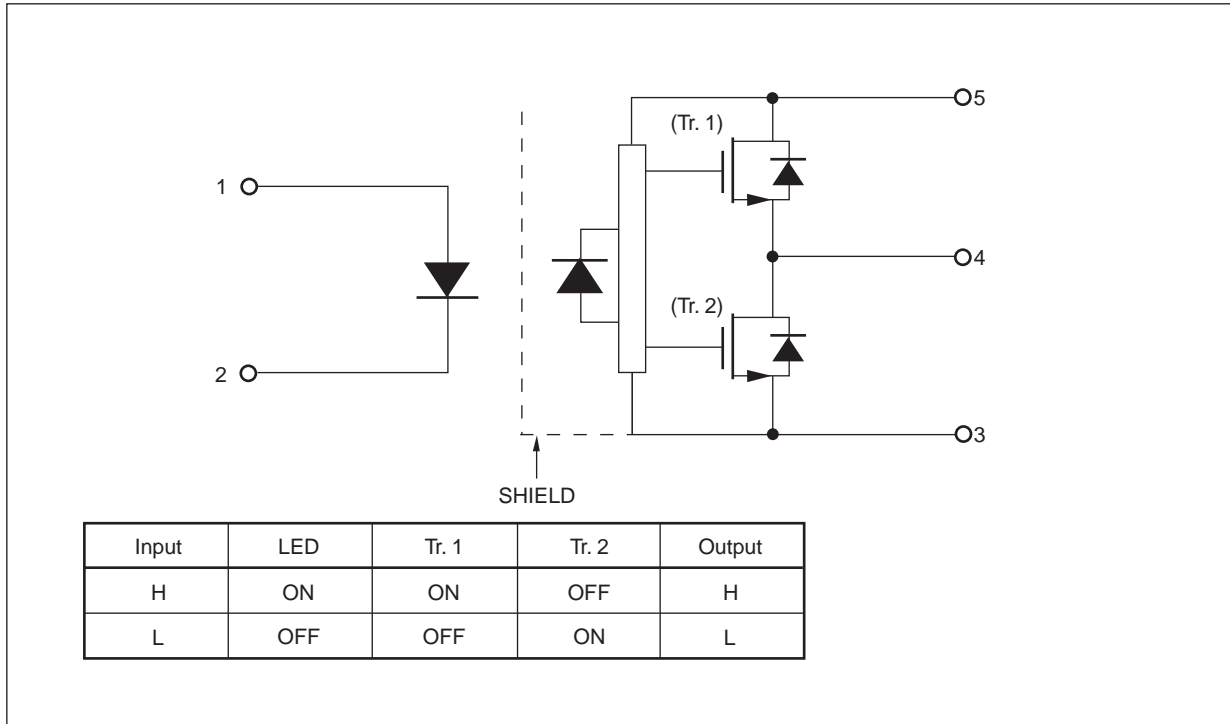


Weight: 0.119g (typ.)

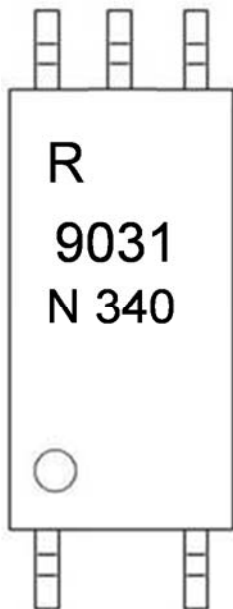
## PHOTOCOUPLER CONSTRUCTION

Parameter	MIN.
Air Distance	8.0 mm
Outer Creepage Distance	8.0 mm
Isolation Distance	0.15 mm

**BLOCK DIAGRAM**



**MARKING EXAMPLE**



R	An initial of "Renesas"	
9031	Product Part Number	
○	No.1 pin Mark, Anode Mark	
N340	N	Rank Code
		340
	3	Last one-digit of Assembly Year
		40

## ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number <sup>*1</sup>
PS9031	PS9031-Y-AX	Pb-Free and Halogen Free (Ni/Pd/Au)	20 pcs (Tape 20 pcs cut)	Standard products (UL, CSA approved)	PS9031
PS9031-F3	PS9031-Y-F3-AX		Embossed Tape 3 000 pcs/reel		
PS9031-V	PS9031-Y-V-AX		20 pcs (Tape 20 pcs cut)	UL, CSA approved DIN EN 60747-5-5 (VDE 0884-5): 2011-11 approved (Option)	
PS9031-V-F3	PS9031-Y-V-F3-AX		Embossed Tape 3 000 pcs/reel		

Note: \*1. For the application of the Safety Standard, following part number should be used.

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current	$I_F$	25	mA
	Peak Transient Forward Current (Pulse Width < 1 $\mu\text{s}$ )	$I_{F(\text{TRAN})}$	1.0	A
	Reverse Voltage	$V_R$	5	V
	Power Dissipation <sup>*1</sup>	$P_D$	45	mW
Detector	High Level Peak Output Current <sup>*2</sup>	$I_{OH(\text{PEAK})}$	2.5	A
	Low Level Peak Output Current <sup>*2</sup>	$I_{OL(\text{PEAK})}$	2.5	A
	Supply Voltage	$(V_{CC} - V_{EE})$	0 to 35	V
	Output Voltage	$V_O$	0 to $V_{CC}$	V
	Power Dissipation <sup>*3</sup>	$P_C$	250	mW
Isolation Voltage <sup>*4</sup>		BV	5 000	Vr.m.s.
Operating Frequency		f	200	kHz
Operating Ambient Temperature		$T_A$	-40 to +125	$^\circ\text{C}$
Storage Temperature		$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

Notes: \*1. Reduced to 1.2 mW/ $^\circ\text{C}$  at  $T_A = 110^\circ\text{C}$  or more.

\*2. Maximum pulse width = 10  $\mu\text{s}$ , Maximum duty cycle = 0.2%

\*3. Reduced to 3.9 mW/ $^\circ\text{C}$  at  $T_A = 90^\circ\text{C}$  or more.

\*4. AC voltage for 1 minute at  $T_A = 25^\circ\text{C}$ , RH = 60% between input and output.

Pins 1-2 shorted together, 3-5 shorted together.

## RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	$(V_{CC} - V_{EE})$	15		30	V
Forward Current (ON)	$I_{F(\text{ON})}$	8	10	12	mA
Forward Voltage (OFF)	$V_{F(\text{OFF})}$	-2		0.8	V
Operating Ambient Temperature	$T_A$	-40		125	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS**(at RECOMMENDED OPERATING CONDITIONS,  $V_{EE}=GND$ , unless otherwise Specified)

Parameter		Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit
Diode	Forward Voltage	$V_F$	$I_F = 10 \text{ mA}$ , $T_A = 25^\circ\text{C}$	1.35	1.56	1.75	V
	Reverse Current	$I_R$	$V_R = 3 \text{ V}$ , $T_A = 25^\circ\text{C}$			10	$\mu\text{A}$
	Input Capacitance	$C_{IN}$	$f = 1 \text{ MHz}$ , $V_F = 0 \text{ V}$		30		pF
Detector	High Level Output Current	$I_{OH}$	$V_O = (V_{CC} - 4 \text{ V})^{*2}$	0.5	2.2		A
			$V_O = (V_{CC} - 15 \text{ V})^{*3}$	2.0			
	Low Level Output Current	$I_{OL}$	$V_O = (V_{EE} + 2.5 \text{ V})^{*2}$	0.5	2.4		A
			$V_O = (V_{EE} + 15 \text{ V})^{*3}$	2.0			
	High Level Output Voltage	$V_{OH}$	$I_O = -100 \text{ mA}^{*4}$	$V_{CC} - 3.0$	$V_{CC} - 1.3$		V
	Low Level Output Voltage	$V_{OL}$	$I_O = 100 \text{ mA}$		0.2	0.5	V
	High Level Supply Current	$I_{CCH}$	$V_O = \text{Open}$ , $I_F = 10 \text{ mA}$		1.7	2.2	mA
	Low Level Supply Current	$I_{CCL}$	$V_O = \text{Open}$ , $V_F = 0 \text{ to } 0.8\text{V}$		1.7	2.2	mA
	UVLO Threshold	$V_{UVLO+}$	$V_O > 5 \text{ V}$ , $I_F = 10 \text{ mA}$	10.8	12.3	13.4	V
$V_{UVLO-}$		9.5		11.0	12.5		
UVLO Hysteresis	$UVLO_{HYS}$	$V_O > 5 \text{ V}$ , $I_F = 10 \text{ mA}$	0.4	1.3		V	
Coupled	Threshold Input Current (L $\rightarrow$ H)	$I_{FLH}$	$I_O = 0 \text{ mA}$ , $V_O > 5 \text{ V}$		1.7	4.0	mA
	Threshold Input Voltage (H $\rightarrow$ L)	$V_{FHL}$	$I_O = 0 \text{ mA}$ , $V_O < 5 \text{ V}$	0.8			V

Notes: \*1. Typical values at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} - V_{EE} = 30 \text{ V}$ .\*2. Maximum pulse width = 50  $\mu\text{s}$ , Maximum duty cycle = 0.5%.\*3. Maximum pulse width = 10  $\mu\text{s}$ , Maximum duty cycle = 0.2%.\*4.  $V_{OH}$  is measured with the DC load current in this testing (Maximum pulse width = 2 ms, Maximum duty cycle = 20%).**SWITCHING CHARACTERISTICS**(at RECOMMENDED OPERATING CONDITIONS,  $V_{EE}=GND$ , unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit	
Propagation Delay Time (L $\rightarrow$ H)	$t_{PLH}$	$R_g = 10 \Omega$ , $C_g = 10 \text{ nF}$ , $f = 10 \text{ kHz}$ , Duty Cycle = 50%, $I_F = 10 \text{ mA}$		80	175	ns	
Propagation Delay Time (H $\rightarrow$ L)	$t_{PHL}$			105	175	ns	
Pulse Width Distortion (PWD)	$ t_{PHL} - t_{PLH} $				25	75	ns
Propagation Delay Time (Difference Between Any Two Products)	$t_{PHL} - t_{PLH}$			-90		90	ns
Rise Time	$t_r$				40		ns
Fall Time	$t_f$				40		ns
Common Mode Transient Immunity at High Level Output	$ CM_H $		$T_A = 25^\circ\text{C}$ , $I_F = 10 \text{ mA}$ , $V_{CC} = 30 \text{ V}$ , $V_{CM} = 1.5 \text{ kV}$	50			$\text{kV}/\mu\text{s}$
Common Mode Transient Immunity at Low Level Output	$ CM_L $	$T_A = 25^\circ\text{C}$ , $I_F = 0 \text{ mA}$ , $V_{CC} = 30 \text{ V}$ , $V_{CM} = 1.5 \text{ kV}$	50			$\text{kV}/\mu\text{s}$	

Notes: \*1. Typical values at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} - V_{EE} = 30 \text{ V}$ .

TEST CIRCUIT

Fig. 1  $I_{OH}$  Test Circuit

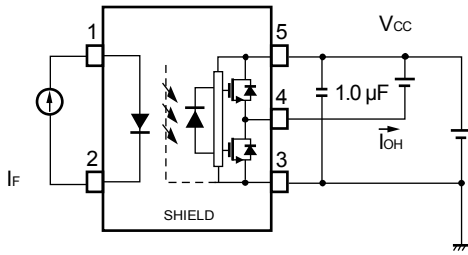


Fig. 2  $I_{OL}$  Test Circuit

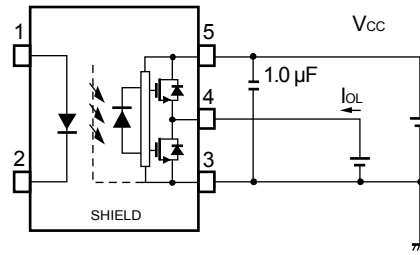


Fig. 3  $V_{OH}$  Test Circuit

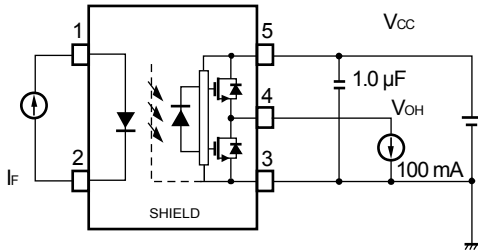


Fig. 4  $V_{OL}$  Test Circuit

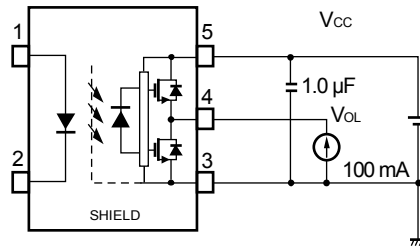


Fig. 5  $I_{CCH}/I_{CCL}$  Test Circuit

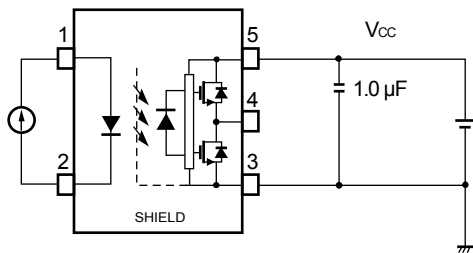


Fig. 6 UVLO Test Circuit

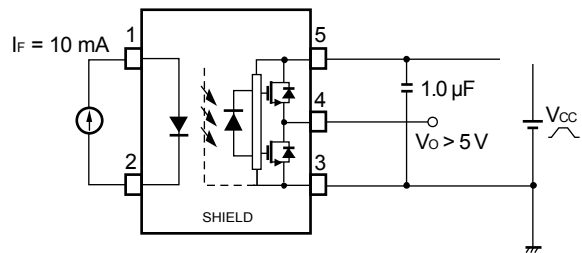


Fig. 7 IFLH Test Circuit

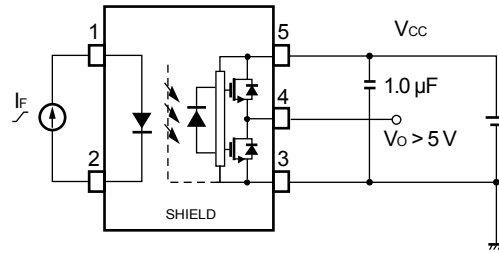


Fig. 8 t<sub>PLH</sub>, t<sub>PHL</sub>, t<sub>r</sub>, t<sub>f</sub> Test Circuit and Wave Forms

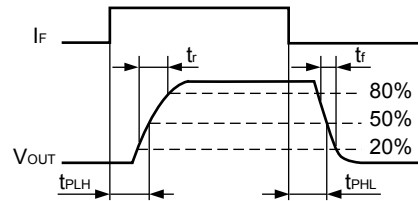
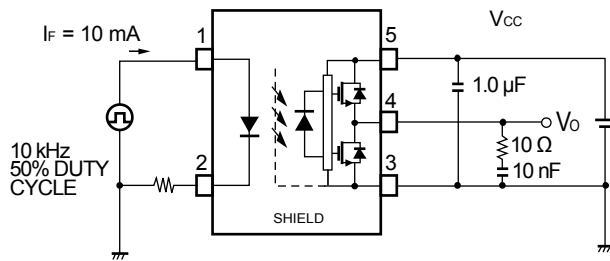
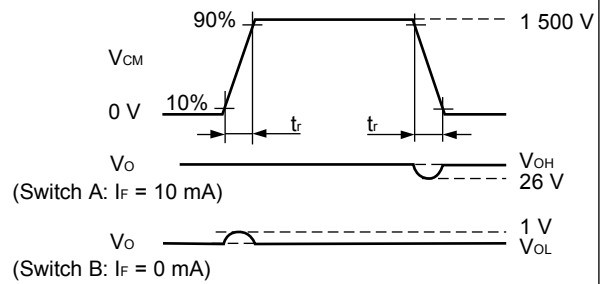
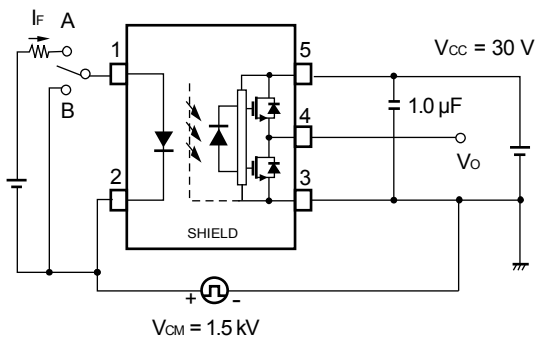
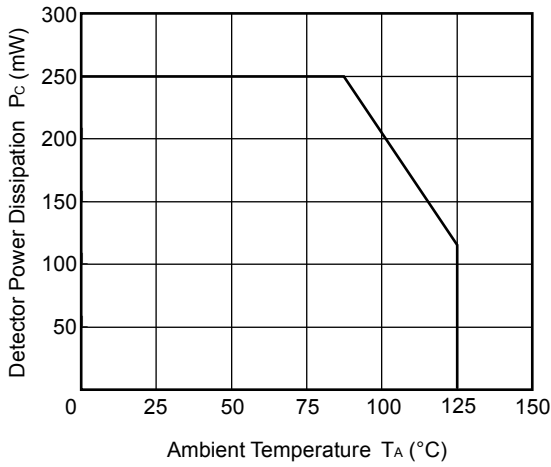


Fig. 9 CMR Test Circuit and Wave Forms

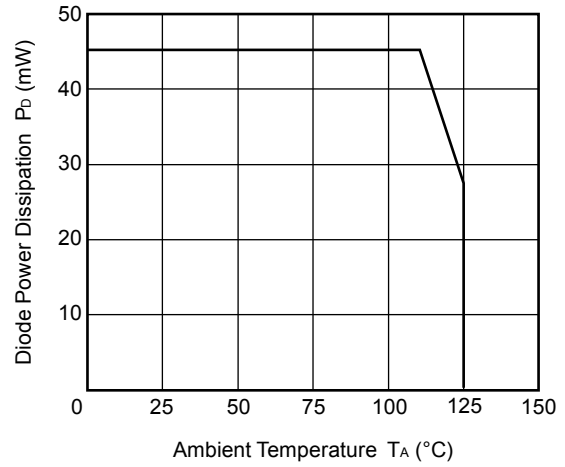


**TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)**

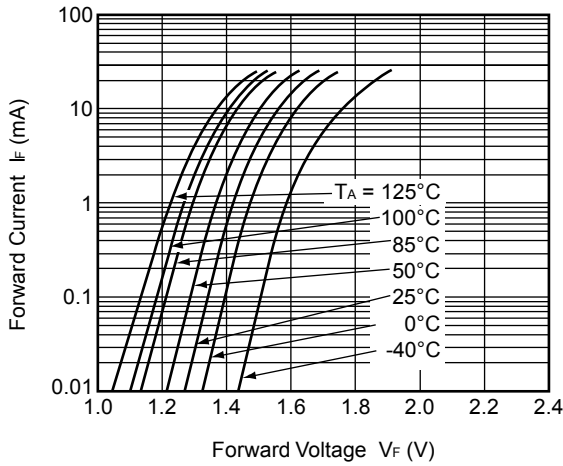
**DETECTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE**



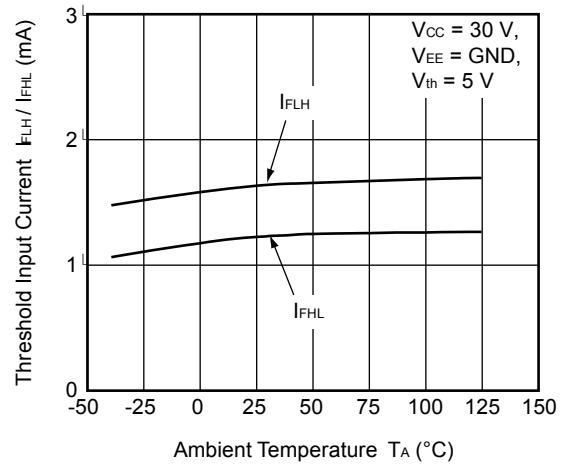
**DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE**



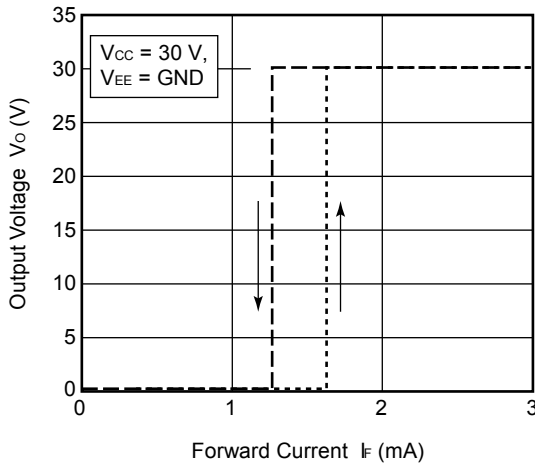
**FORWARD CURRENT vs. FORWARD VOLTAGE**



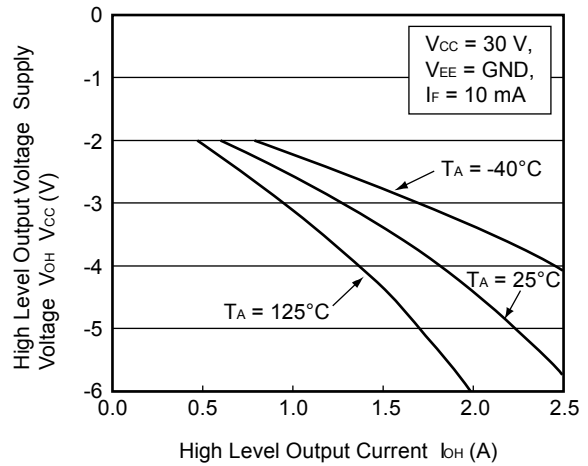
**THRESHOLD INPUT CURRENT vs. AMBIENT TEMPERATURE**



**OUTPUT VOLTAGE vs. FORWARD CURRENT**



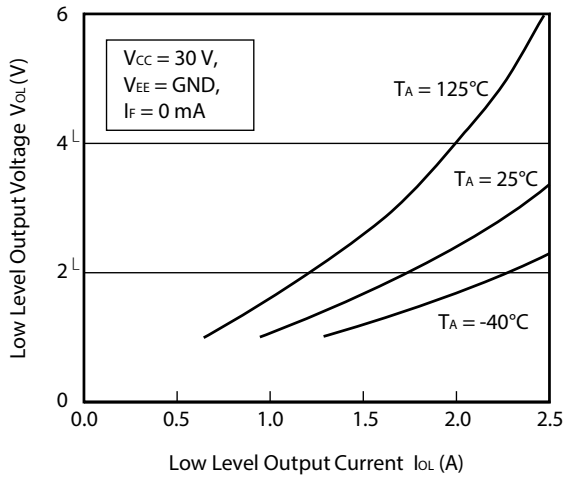
**HIGH LEVEL OUTPUT VOLTAGE SUPPLY VOLTAGE vs. HIGH LEVEL OUTPUT CURRENT**



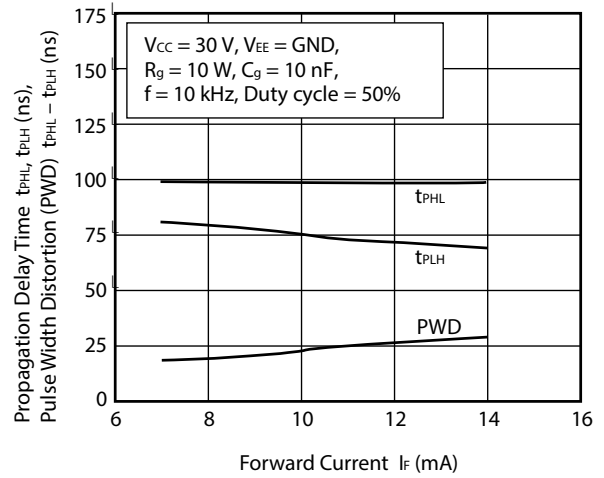
**Remark** The graphs indicate nominal characteristics.



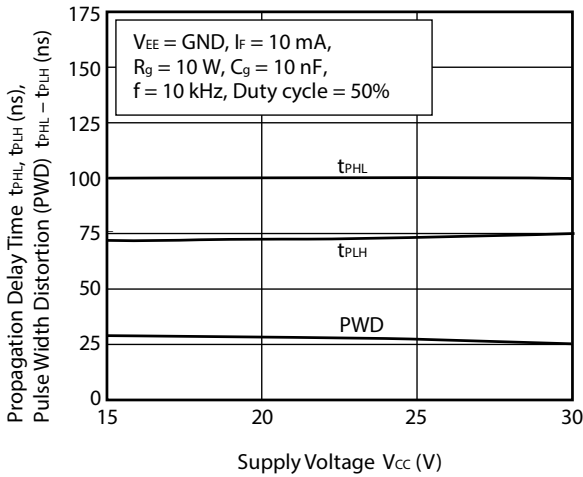
LOW LEVEL OUTPUT VOLTAGE vs. LOW LEVEL OUTPUT CURRENT



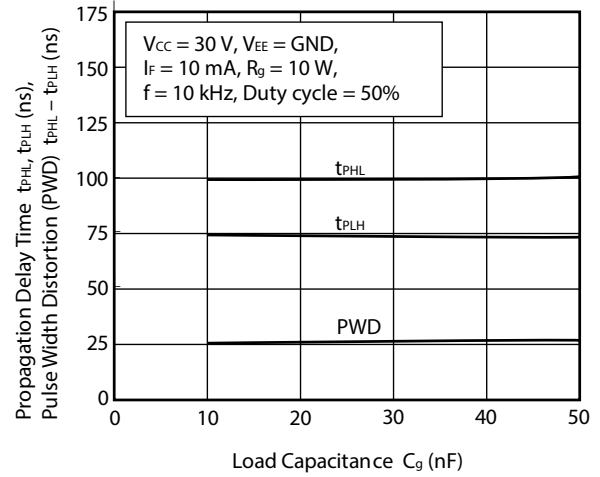
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. FORWARD CURRENT



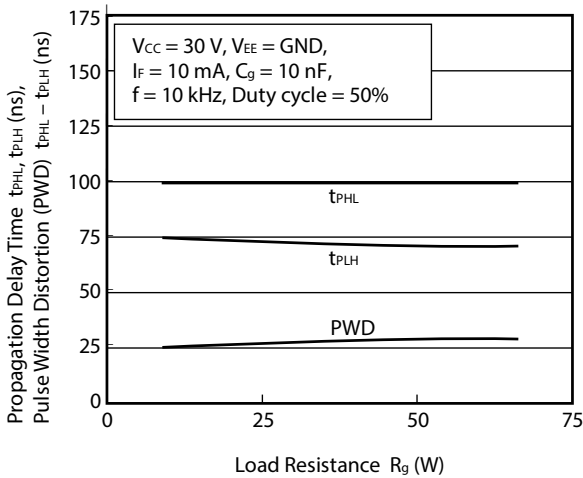
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. SUPPLY VOLTAGE



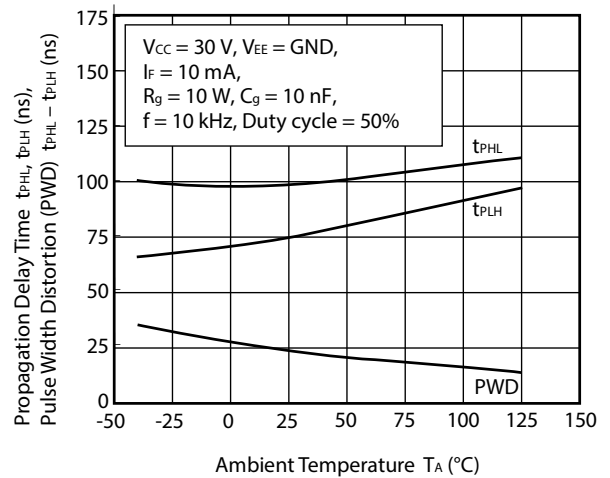
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD CAPACITANCE



PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD RESISTANCE

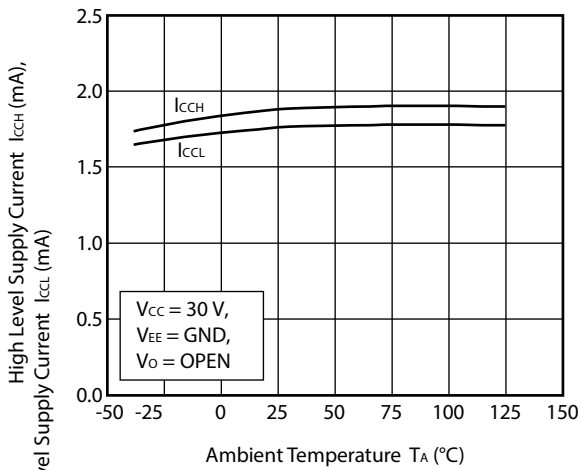


PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. AMBIENT TEMPERATURE

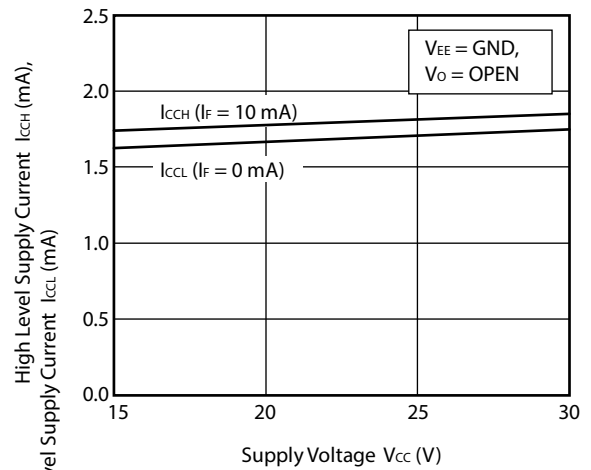


**Remark** The graphs indicate nominal characteristics.

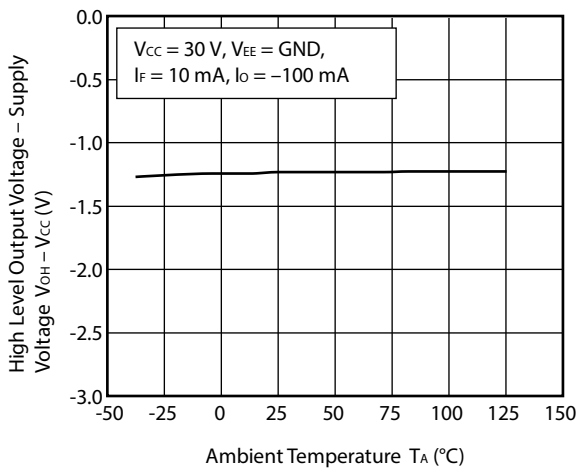
SUPPLY CURRENT vs. AMBIENT TEMPERATURE



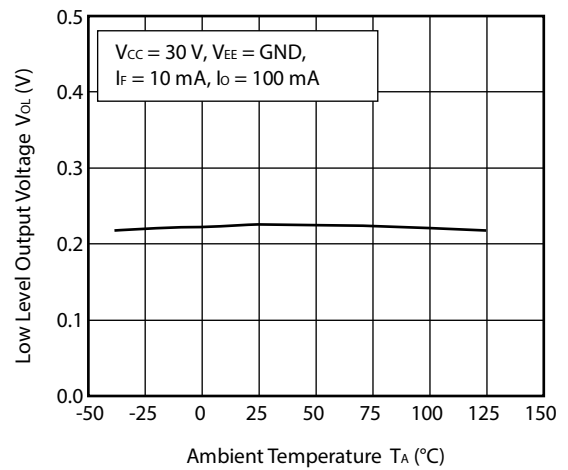
SUPPLY CURRENT vs. SUPPLY VOLTAGE



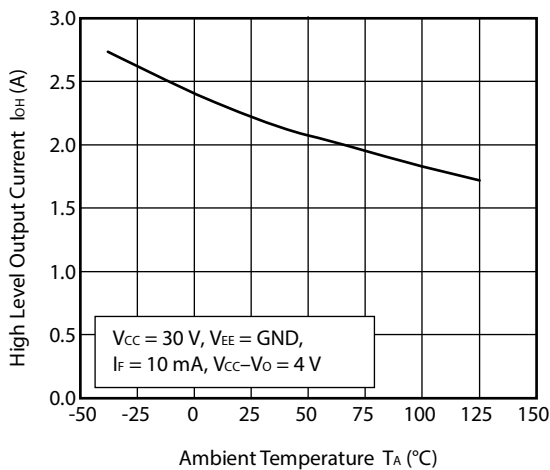
HIGH LEVEL OUTPUT VOLTAGE – SUPPLY VOLTAGE vs. AMBIENT TEMPERATURE



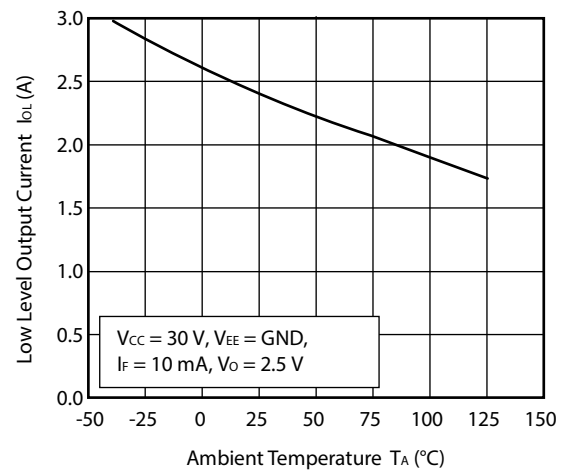
LOW LEVEL OUTPUT VOLTAGE vs. AMBIENT TEMPERATURE



HIGH LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

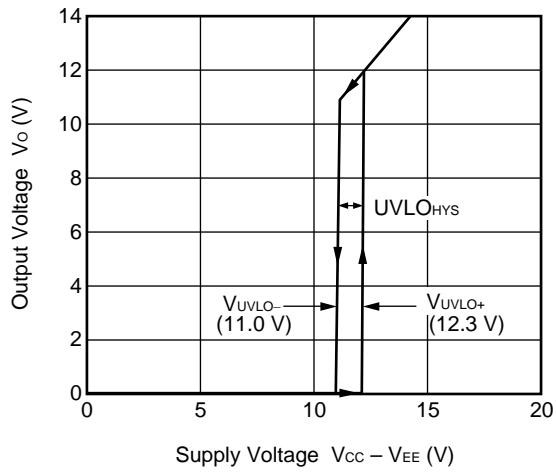


LOW LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE



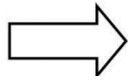
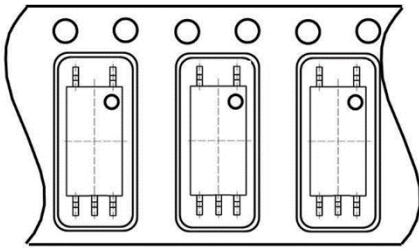
**Remark** The graphs indicate nominal characteristics.

OUTPUT VOLTAGE vs. SUPPLY VOLTAGE



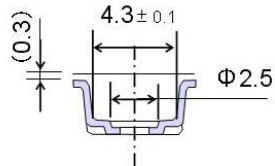
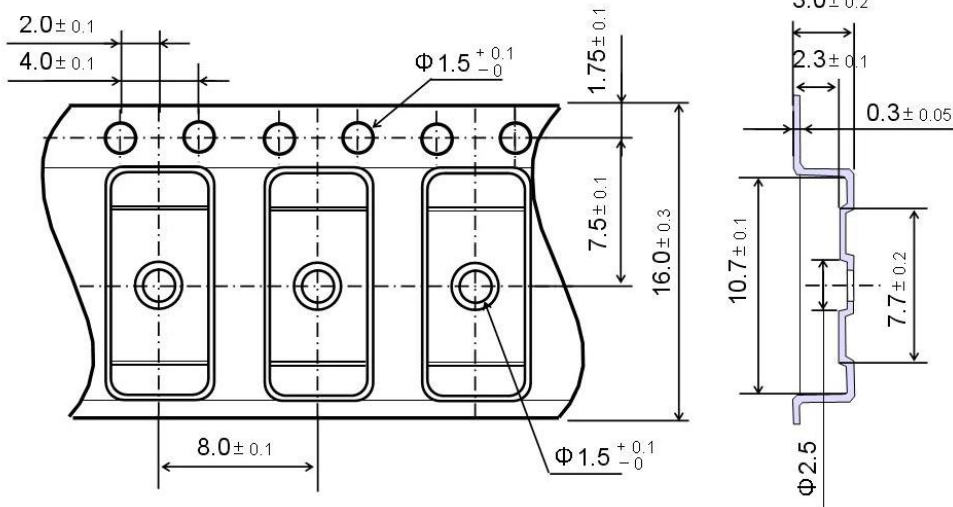
**Remark** The graphs indicate nominal characteristics.

TAPING SPECIFICATIONS (UNIT: mm)

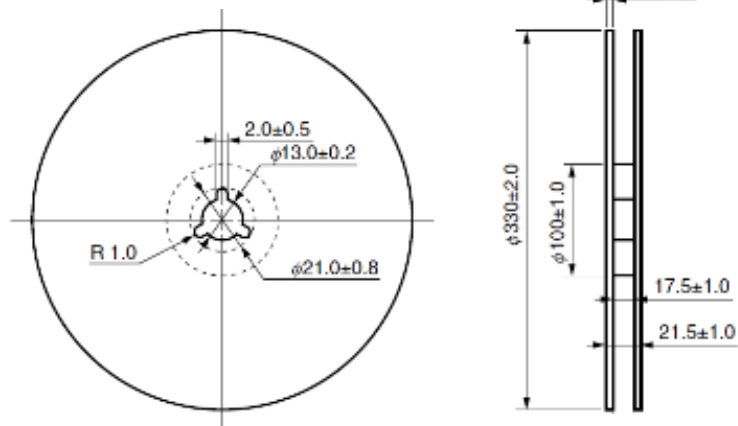


Tape Direction

Outline and Dimensions (Taps)

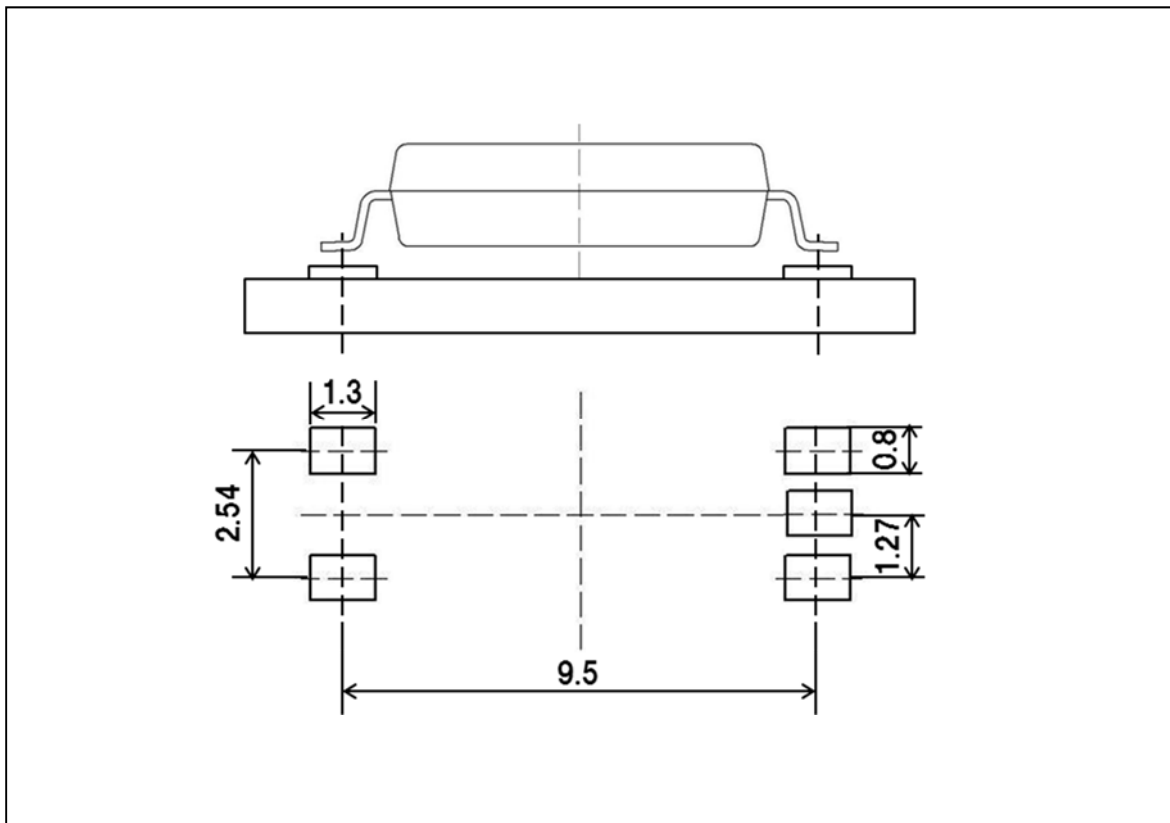


Outline and Dimensions (Reel)



Packing: 3000 pcs/reel

## RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)



**Remark** All dimensions in this figure must be evaluated before use.

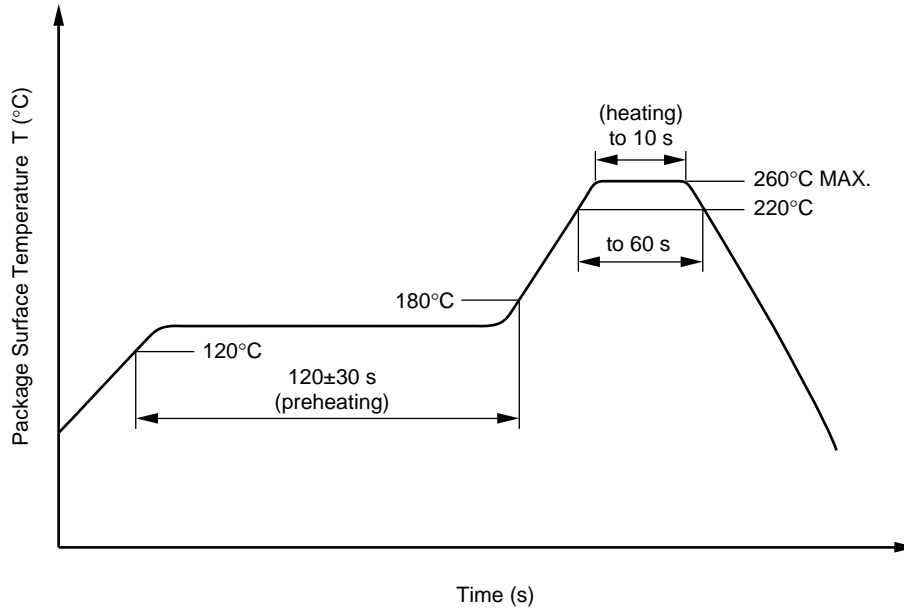
## NOTES ON HANDLING

### 1. Recommended soldering conditions

#### (1) Infrared reflow soldering

- Peak reflow temperature 260°C or below (package surface temperature)
- Time of peak reflow temperature 10 seconds or less
- Time of temperature higher than 220°C 60 seconds or less
- Time to preheat temperature from 120 to 180°C 120±30 s
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



#### (2) Wave soldering

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

#### (3) Soldering by Soldering Iron

- Peak Temperature (lead part temperature) 350°C or below
- Time (each pins) 3 seconds or less
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead

#### (4) Cautions

- Fluxes Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

### 2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

## USAGE CAUTIONS

1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
2. Board designing
  - (1) By-pass capacitor of more than 1.0  $\mu\text{F}$  is used between VCC and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
  - (2) When designing the printed wiring board, ensure that the pattern of the IGBT collectors/emitters is not too close to the input block pattern of the photocoupler.

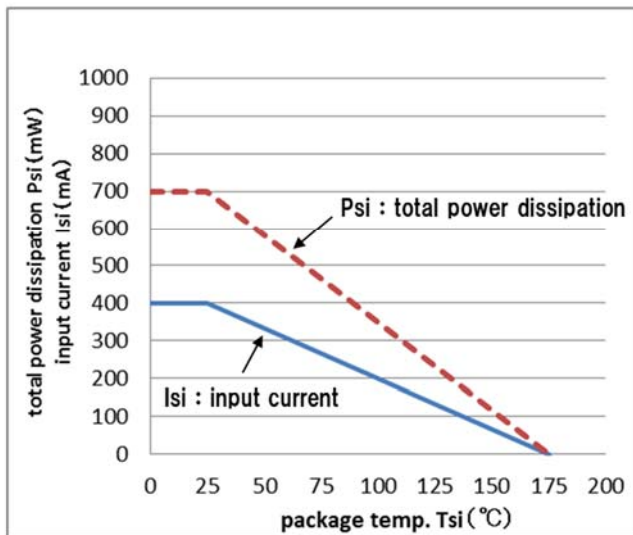
If the pattern is too close to the input block and coupling occurs, a sudden fluctuation in the voltage on the IGBT output side might affect the photocoupler's LED input, leading to malfunction or degradation of characteristics.

(If the pattern needs to be close to the input block, to prevent the LED from lighting during the off state due to the abovementioned coupling, design the input-side circuit so that the bias of the LED is reversed, within the range of the recommended operating conditions, and be sure to thoroughly evaluate operation.)
3. Make sure the rise/fall time of the forward current is 0.5  $\mu\text{s}$  or less.
4. In order to avoid malfunctions, make sure the rise/fall slope of the supply voltage is 3 V/ $\mu\text{s}$  or less.
5. Avoid storage at a high temperature and high humidity.

**SPECIFICATION OF VDE MARKS LICENSE DOCUMENT**

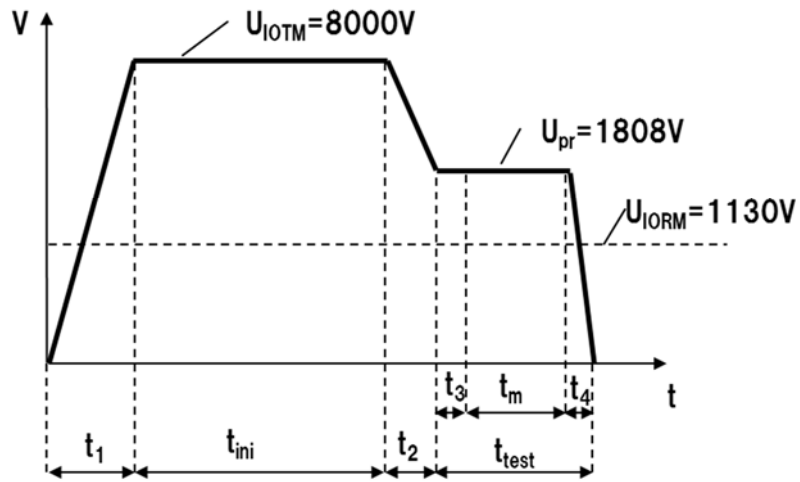
Parameter	Symbol	Spec.	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/125/21	
Dielectric strength maximum operating isolation voltage Test voltage (partial discharge test, procedure a for type test and random test) $U_{pr} = 1.6 \times U_{IORM}, P_d < 5 \text{ pC}$	$U_{IORM}$ $U_{pr}$	1 130 1 808	$V_{peak}$ $V_{peak}$
Test voltage (partial discharge test, procedure b for all devices) $U_{pr} = 1.875 \times U_{IORM}, P_d < 5 \text{ pC}$	$U_{pr}$	2 119	$V_{peak}$
Highest permissible overvoltage	$U_{IOTM}$	8 000	$V_{peak}$
Degree of pollution (DIN EN 60664-1 VDE0110 Part 1)		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303 Part 11))	CTI	400	
Material group (DIN EN 60664-1 VDE0110 Part 1)		II	
Storage temperature range	$T_{stg}$	-55 to +150	°C
Operating temperature range	$T_A$	-40 to +125	°C
Isolation resistance, minimum value $V_{IO} = 500 \text{ V dc at } T_A = 25^\circ\text{C}$ $V_{IO} = 500 \text{ V dc at } T_A \text{ MAX. at least } 100^\circ\text{C}$	Ris MIN. Ris MIN.	$10^{12}$ $10^{11}$	$\Omega$ $\Omega$
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature Current (input current $I_F$ , $P_{si} = 0$ ) Power (output or total power dissipation) Isolation resistance $V_{IO} = 500 \text{ V dc at } T_A = T_{si}$	$T_{si}$ $I_{si}$ $P_{si}$ Ris MIN.	175 400 700 $10^9$	°C mA mW $\Omega$

**Dependence of maximum safety ratings with package temperature**



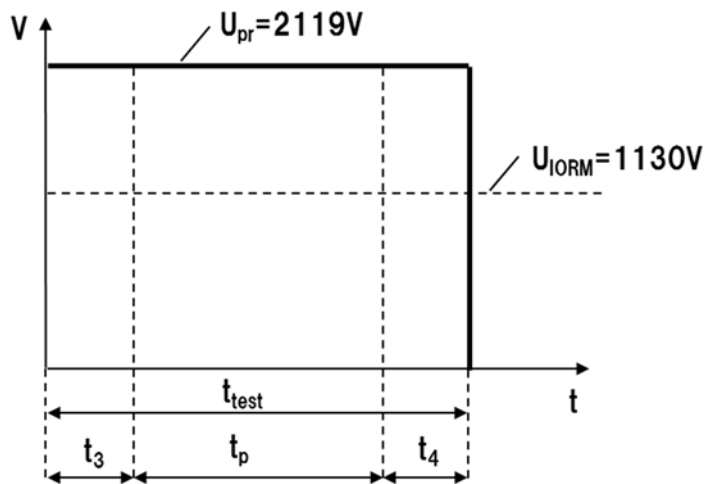


Method A Destructive Test, Type and Sample test



$t_1, t_2 = 1$  to  $10$  sec  
 $t_3, t_4 = 1$  sec  
 $t_m$  (PARTIAL DISCHARGE) =  $10$  sec  
 $t_{test} = 12$  sec  
 $t_{ini} = 60$  sec

Method b Non-destructive Test, 100% Production Test



$t_3, t_4 = 0.1$  sec  
 $t_p$  (PARTIAL DISCHARGE) =  $1.0$  sec  
 $t_{test} = 1.2$  sec

<b>Caution</b>	GaAs Products	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"><li>• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.<ol style="list-style-type: none"><li>1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.</li><li>2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.</li></ol></li><li>• Do not burn, destroy, cut, crush, or chemically dissolve the product.</li><li>• Do not lick the product or in any way allow it to enter the mouth.</li></ul>
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